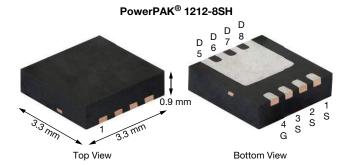
# SiSH110DN

www.vishay.com

**Vishay Siliconix** 

## N-Channel 20 V (D-S) Fast Switching MOSFET



20

0.0053

0.0078

14

21.1

Single

**PRODUCT SUMMARY** 

 $R_{DS(on)}$  max. ( $\Omega$ ) at  $V_{GS}$  = 10 V

 $R_{DS(on)}$  max. ( $\Omega$ ) at  $V_{GS} = 4.5$  V

V<sub>DS</sub> (V)

 $I_D(A)$ 

Q<sub>g</sub> typ. (nC)

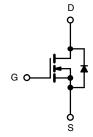
Configuration

**FEATURES** 

- TrenchFET<sup>®</sup> Gen II power MOSFET
- PWM optimized
- 100 % R<sub>g</sub> tested
- Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>

### **APPLICATIONS**

- Synchronous rectification
- Synchronous buck



N-Channel MOSFET

ORDERING INFORMATION	
Package	PowerPAK 1212-8
Lead (Pb)-free and halogen-free	SiSH110DN-T1-GE3

ABSOLUTE MAXIMUM RATINGS (	T <sub>A</sub> = 25 °C, unless	otherwise no	ted)			
PARAMETER		SYMBOL	10 s	STEADY STATE	UNIT	
Drain-source voltage		V <sub>DS</sub>	20	20	V	
Gate-source voltage		V <sub>GS</sub>	± 20	± 20	V	
Continuous drain surrant (T = $150 ^{\circ}$ C) a	T <sub>A</sub> = 25 °C	I	21.1	13.5		
Continuous drain current ( $T_J = 150 \ ^{\circ}C$ ) <sup>a</sup>	T <sub>A</sub> = 70 °C	I <sub>D</sub>	16.9	10.8		
Pulsed drain current		I <sub>DM</sub>	60	60	A	
Continuous source current (diode conduction) <sup>a</sup>		I <sub>S</sub>	3.2	1.3		
Single avalanche current			35	35		
Single avalanche energy	L = 0 1 mH	E <sub>AS</sub>	61	61	mJ	
Marian and a surger disation of	T <sub>A</sub> = 25 °C		3.8	1.5	14/	
Maximum power dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C	PD	2	0.8	W	
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150		°C	
Soldering recommendations (peak temperature) <sup>b, c</sup>			260			

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient <sup>a</sup>	t ≤ 10 s	Р	24	33	
	Steady state	R <sub>thJA</sub>	65	81	°C/W
Maximum junction-to-case (drain)	Steady state	R <sub>thJC</sub>	1.9	2.4	

#### Notes

a. Surface mounted on 1" x 1" FR4 board

b. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK 1212-8SH is a leadless package within the PowerPAK 1212-8 package family. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
c. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

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### For technical questions, contact: pmostechsupport@vishay.com

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RoHS COMPLIANT HALOGEN

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SiSH110DN

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<b>SPECIFICATIONS</b> (T <sub>J</sub> = 25 $^{\circ}$ C	, unless oth	nerwise noted)				
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Gate threshold voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 250 \ \mu A$	1.5	-	2.5	V
Gate-body leakage	I <sub>GSS</sub>			-	± 100	nA
Zero gate voltage drain current	1	$V_{DS} = 20 V, V_{GS} = 0 V$	-	-	1	μA
Zero gate voltage drain current	IDSS	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$	-	-	5	μπ
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	40	-	-	А
Drain-source on-state resistance <sup>a</sup>	P	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 21.1 \text{ A}$	D = 21.1 A - 0.0044		0.0053	Ω
	R <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 17.4 \text{ A}$	-	0.0064	0.0078	52
Forward transconductance a	g <sub>fs</sub>	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 21.1 \text{ A}$	-	71	-	S
Diode forward voltage <sup>a</sup>	V <sub>SD</sub>	$I_{S} = 3.2 \text{ A}, V_{GS} = 0 \text{ V}$	-	0.8	1.2	V
Dynamic <sup>b</sup>						
Total gate charge	Qg		-	14	21	
Gate-source charge	Q <sub>gs</sub>		-	7	-	nC
Gate-drain charge	Q <sub>gd</sub>		-	4.5	-	1
Gate resistance	Rg	f = 1 MHz	0.7	1.4	2.1	Ω
Turn-on delay time	t <sub>d(on)</sub>		-	12	20	
Rise time	t <sub>r</sub>	$V_{DD}$ = 10 V, $R_L$ = 10 $\Omega$	-	10	15	ns
Turn-off delay time	t <sub>d(off)</sub>	$I_D \cong$ 1 A, $V_{GEN}$ = 10 V, $R_g$ = 6 $\Omega$	-	36	55	
Fall time	t <sub>f</sub>			10	15	
Body diode reverse recovery time	t <sub>rr</sub>		-	30	60	
Body diode reverse recovery charge	Q <sub>rr</sub>	I <sub>F</sub> = 3.2 A, di/dt = 100 A/μs	-	25	50	nC
Reverse recovery fall time	ta	$r_F = 3.2 \text{ A}, \text{ all at } = 100 \text{ A/} \mu \text{s}$	-	14	-	20
Reverse recovery rise time	t <sub>b</sub>		-	16	-	ns

#### Notes

a. Pulse test; pulse width  $\leq$  300  $\mu s,$  duty cycle  $\leq$  2 %

b. Guaranteed by design, not subject to production testing

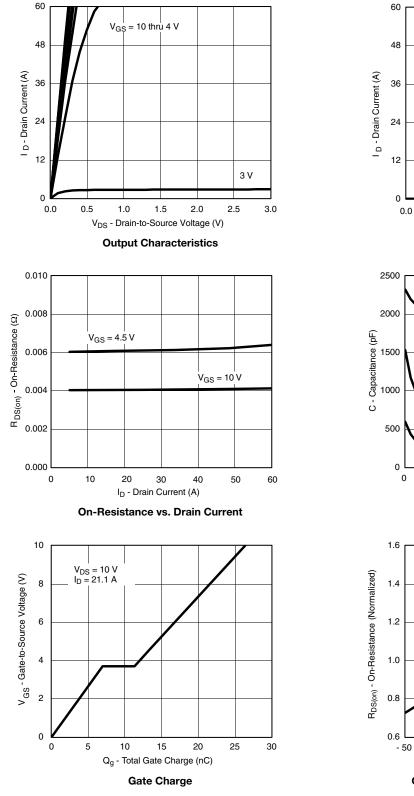
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

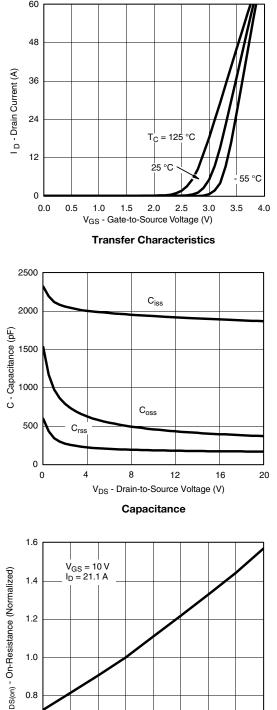
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### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





0 - 25 0 25 50 75 100 125 150 T<sub>J</sub> - Junction Temperature (°C)

**On-Resistance vs. Junction Temperature** 

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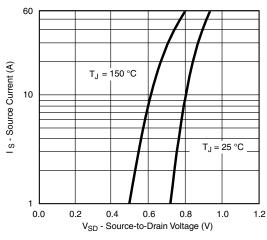
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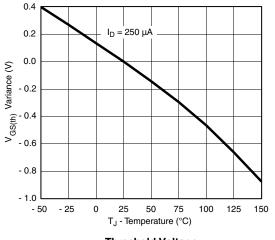
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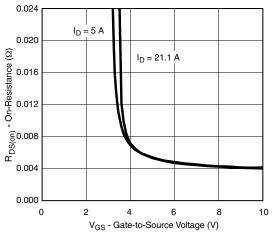
### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



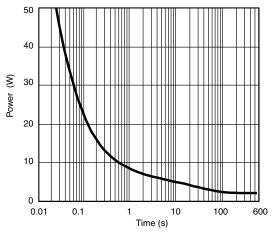
Source-Drain Diode Forward Voltage



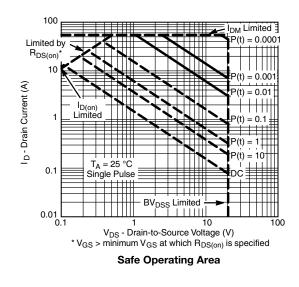




**On-Resistance vs. Gate-to-Source Voltage** 



Single Pulse Power, Junction-to-Ambient



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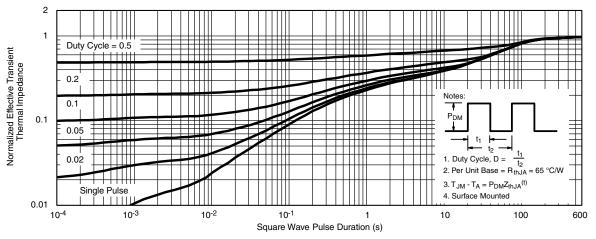
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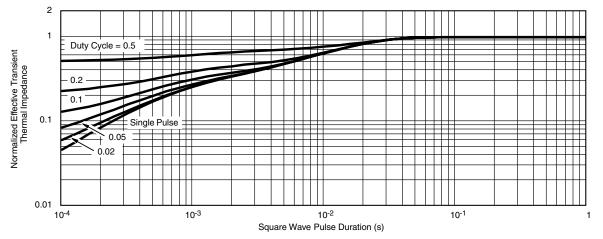


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### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



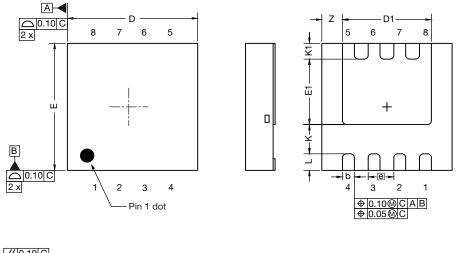
Normalized Thermal Transient Impedance, Junction-to-Case

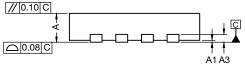
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# Case Outline for PowerPAK<sup>®</sup> 1212-SWLH and PowerPAK<sup>®</sup> 1212-8SH



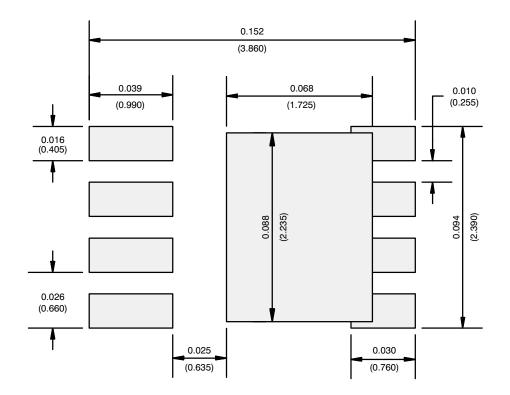


		MILLIMETERS			INCHES	
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
А	0.82	0.90	0.98	0.032	0.035	0.038
A1	0.00	-	0.05	0.000	-	0.002
A3	0.20 ref.				0.008 ref.	
b	0.25	0.30	0.35	0.010	0.012	0.014
D	3.20	3.30	3.40	0.126	0.130	0.134
D1	2.15	2.25	2.35	0.085	0.089	0.093
E	3.20	3.30	3.40	0.126	0.130	0.134
E1	1.60	1.70	1.80	0.063	0.067	0.071
е	0.65 bsc.			0.026 bsc.		
К	0.76 ref.				0.030 ref.	
K1	0.41 ref.			0.016 ref.		
L	0.33	0.43	0.53	0.013	0.017	0.021
Z	0.525 ref.			0.525 ref. 0.021 ref.		

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## RECOMMENDED MINIMUM PADS FOR PowerPAK<sup>®</sup> 1212-8 Single



Recommended Minimum Pads Dimensions in Inches/(mm)

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